

Silicon NPN Power Transistors

2SC2486

DESCRIPTION

- With TO-3PN package
- Complement to type 2SA1062
- High collector power dissipation

APPLICATIONS

- High power audio frequency amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

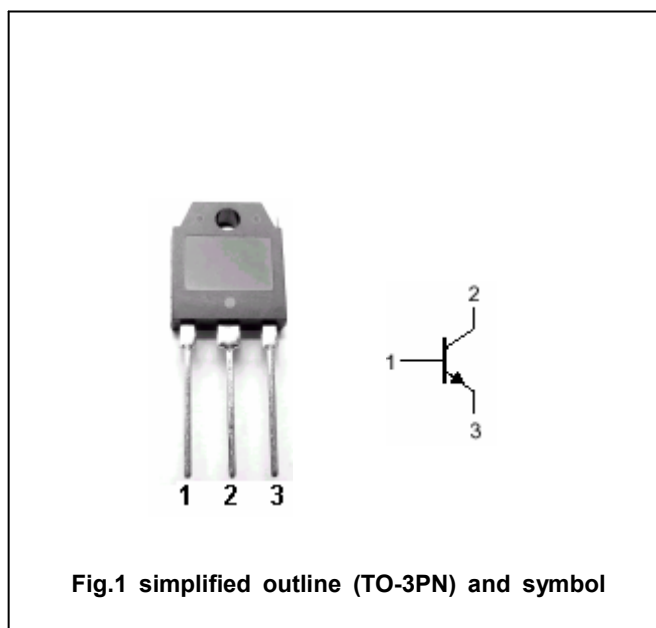


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _{CBO}	Collector-base voltage	Open emitter	120	V
V _{CEO}	Collector-emitter voltage	Open base	120	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current (DC)		7	A
I _{CM}	Collector current-peak		12	A
P _C	Collector power dissipation	T _C =25℃	80	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA ; I _B =0	120			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5A			2.0	V
V _{BE}	Base-emitter on voltage	I _C =5A; V _{CE} =5V			1.8	V
I _{CBO}	Collector cut-off current	V _{CB} =120V; I _E =0			50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =3V; I _C =0			50	μA
h _{FE-1}	DC current gain	I _C =0.02A ; V _{CE} =5V	20			
h _{FE-2}	DC current gain	I _C =1A ; V _{CE} =5V	40		200	
h _{FE-3}	DC current gain	I _C =5A ; V _{CE} =5V	20			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =5V		20		MHz

◆ h_{FE-2} Classifications

R	Q	P
40-80	60-120	100-200

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PACKAGE OUTLINE

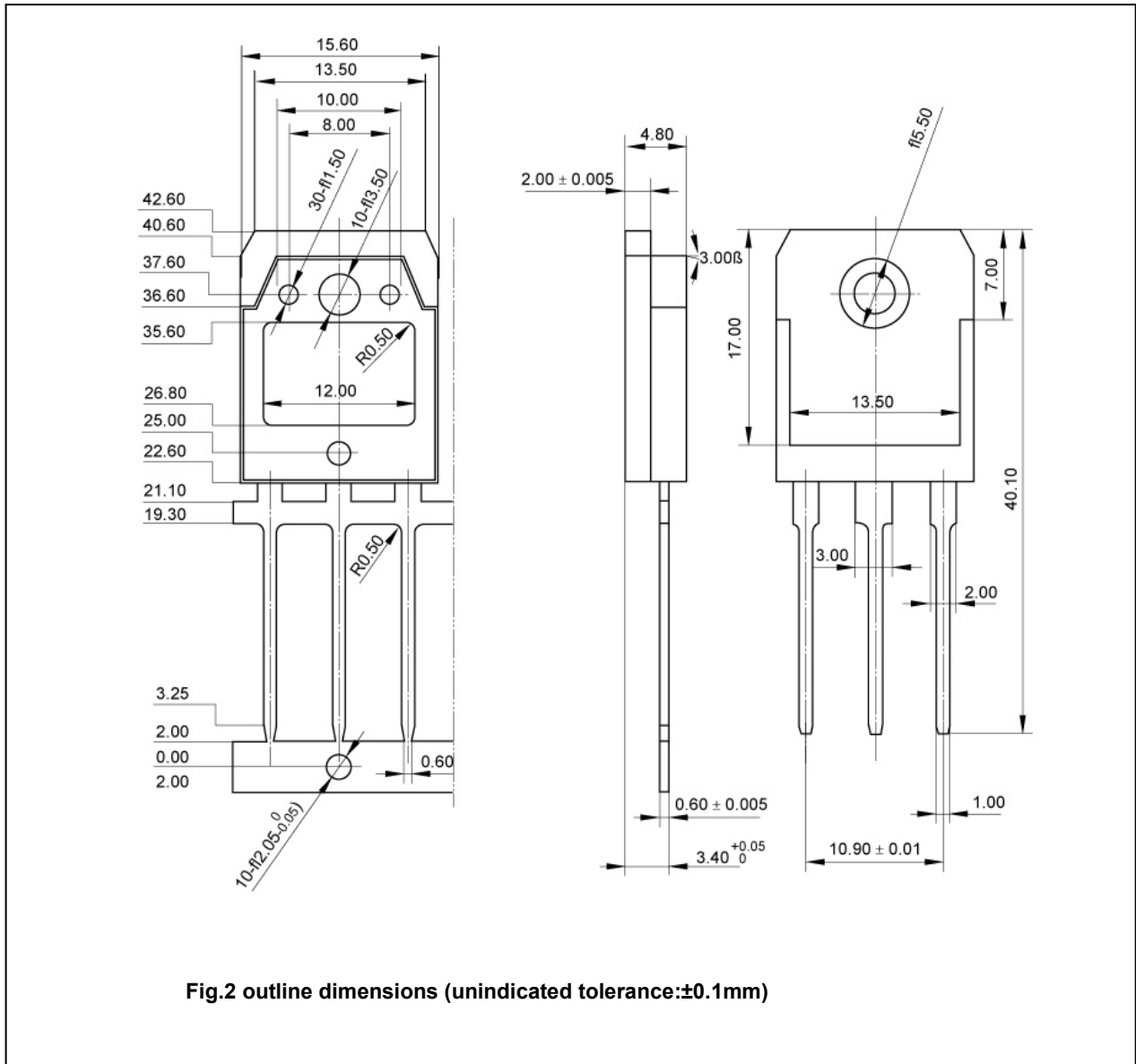


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)